



Etek
Microelectronics

ES4850DFHX

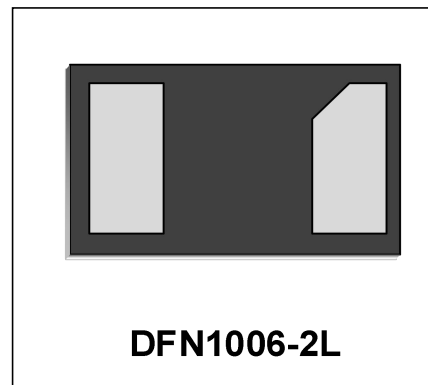
Transient Voltage Suppressor

Features

- 550 Watts Peak Pulse Power per Line ($t_p=8/20\mu s$)
- Small Body Outline Dimensions
- Protects one I/O or power line
- Working Voltage: 4.85V
- Low Leakage Current

IEC COMPATIBILITY (EN61000-4)

- IEC 61000-4-2 (ESD) $\pm 30kV$ (air), $\pm 30kV$ (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 50A (8/20 μs)



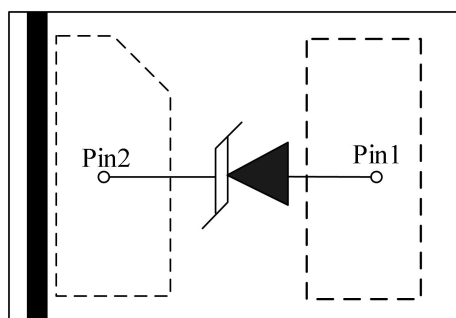
Mechanical Characteristics

- DFN1006-2L package
- Marking : Marking Code
- Packaging : Tape and Reel per EIA 481
- RoHS Compliant
- MSL1

Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants (PDAs)
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras
- MP3 Players

Schematic & PIN Configuration



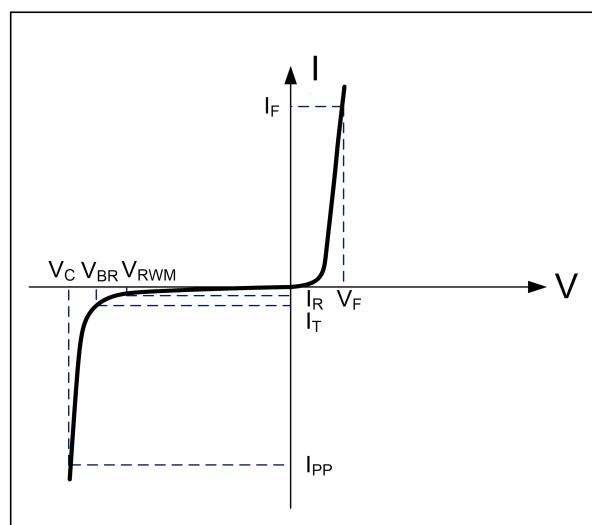
(TOP VIEW)

Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	550	Watts
Peak Pulse Current ($t_p = 8/20\mu s$)	I_{PP}	50	A
Operating Temperature	T_J	-55 to + 125	°C
Storage Temperature	T_{STG}	-55 to +150	°C

Electrical Parameters (T=25°C)

Symbol	Parameter
I_{PP}	Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Reverse Stand-Off Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F



Electrical Characteristics

ES4850DFHX						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V_{RWM}				4.85	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	5		7	V
Reverse Leakage Current	I_R	$V_{RWM} = 4.85V, T = 25^\circ C$			500	nA
Forward Voltage	V_F	$I_F = 10mA$	0.5		1.2	V
Clamping Voltage	V_C	$I_{PP} = 50A, t_p = 8/20\mu s$		9	11	V
Dynamic Resistance ^{1,2}	R_{DYN}	$TLP = 0.2/100ns$		0.05		Ω
ESD Clamping Voltage ¹	V_C	$I_{PP} = 4A, t_p = 0.2/100ns (TLP)$		5.9		V
ESD Clamping Voltage ¹	V_C	$I_{PP} = 16A, t_p = 0.2/100ns (TLP)$		6.5		V
Junction Capacitance	C_j	$V_R = 0V, f = 1MHz$		160	200	pF

Note: 1、TLP Setting : $t_p = 100ns, t_r = 0.2ns, I_{TLP}$ and V_{TLP} sample window: $t_1 = 70ns$ to $t_2 = 90ns$.

2、Dynamic resistance calculated from $I_{PP}=4A$ to $I_{PP}=16A$ using "Best Fit"

Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

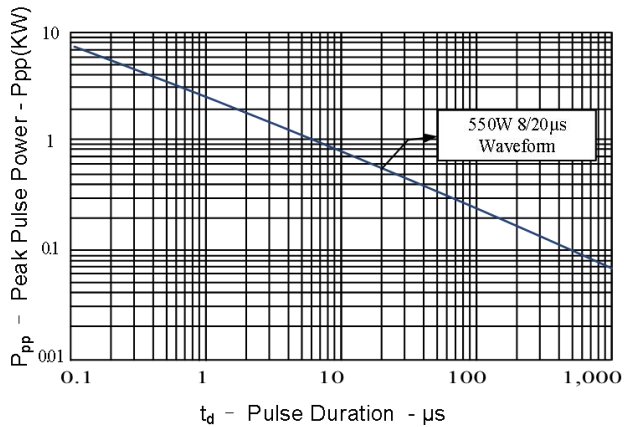


Figure 2: Power Derating Curve

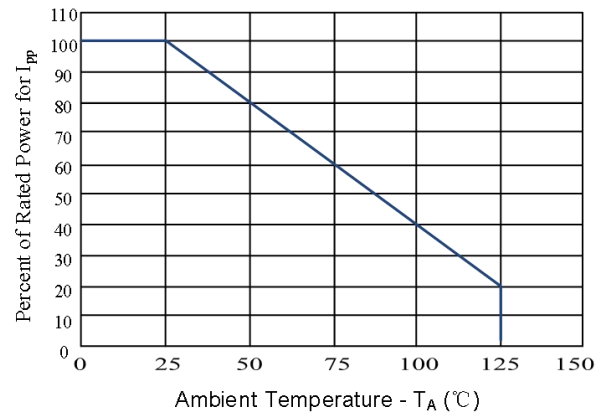


Figure 3: Clamping Voltage vs. Peak Pulse Current

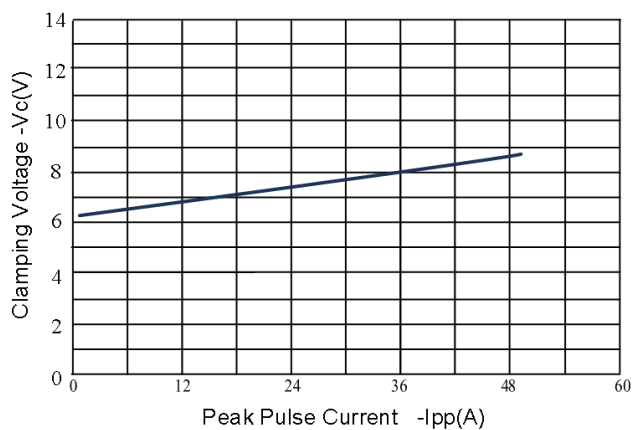


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

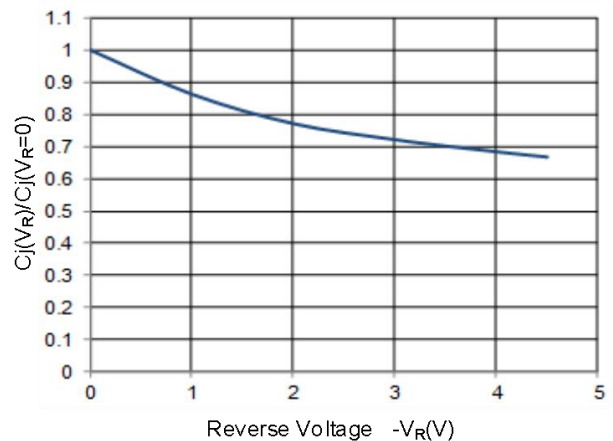


Figure 5: 8/20μs Pulse Waveform

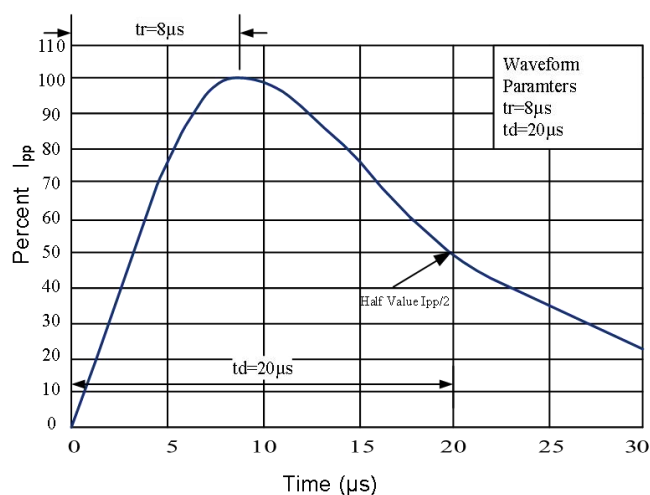
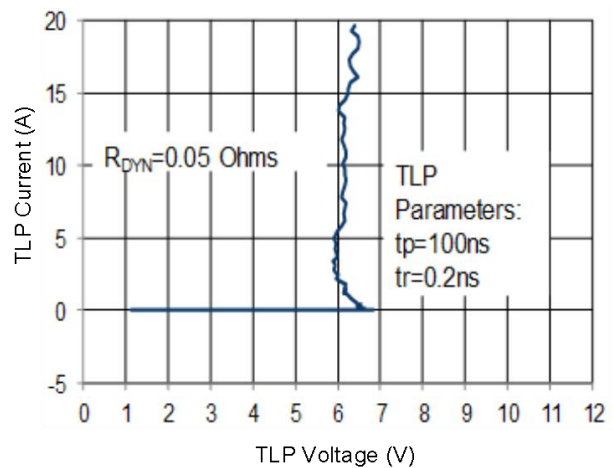
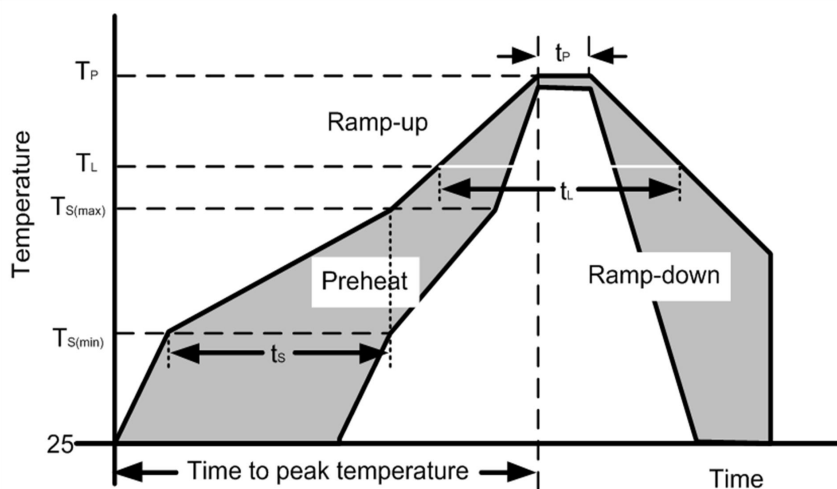


Figure 6: TLP Curve



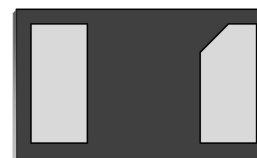
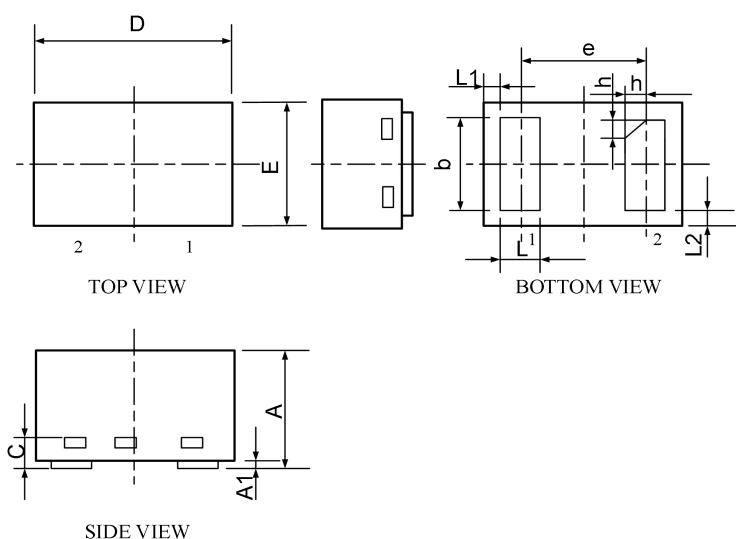
Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ($T_{S(min)}$)	150°C
	Temperature Max ($T_{S(max)}$)	200°C
	Time (min to max) (t_s)	60 – 190 secs
Average ramp up rate (Liquidus Temp) (T_L) to peak		5°C/second max
$T_{S(max)}$ to T_L —Ramp-up Rate		5°C/second max
Reflow	Temperature (T_L) (Liquidus)	217°C
	Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_P)		260+0/-5 °C
Time within actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature (T_P)		8 minutes Max.
Do not exceed		280°C



Outline Drawing –DFN1006-2L

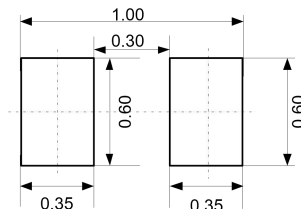
PACKAGE OUTLINE



DFN1006-2L

SYMBOL	MILIMETER		
	MIN	NOM	MAX
A	0.350	-	0.400
A1	0.000	0.020	0.050
b	0.430	0.480	0.530
C	0.127REF		
D	0.950	1.000	1.050
e	0.650BSC		
E	0.550	0.600	0.650
L	0.170	0.220	0.270
L1	0.065REF		
L2	0.060REF		
h	0.075	0.125	0.175

Land Pattern



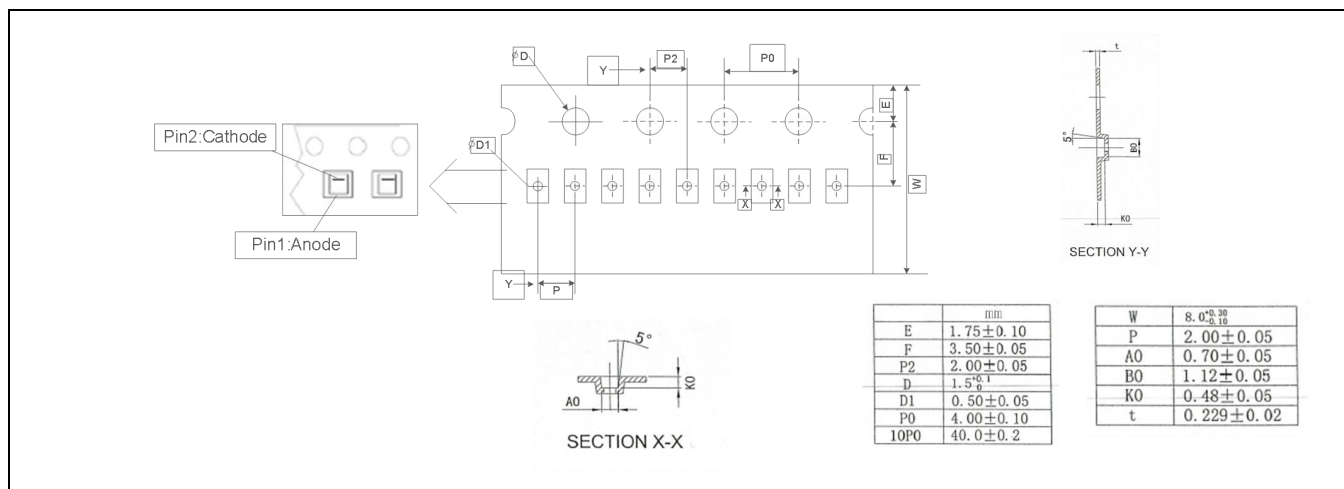
Marking Codes

Part Number	Marking Code
ES4850DFHX	KH=Specific Device Code X=Tracking Number

Package Information

Qty: 10k/Reel

Tape



Revision History

No.	Version	Date	Revision Item	Request	Function and characteristic checking	Package dimension checking	Typos checking
1	1.0	2019-08-02	Released Version	Qi Shu Kun	Qi Shu Kun	Liu Jia Ying	Liu Jia Ying
2	1.1	2020-03-17	Add MSL level	Qi Shu Kun	Qi Shu Kun	Liu Jia Ying	Liu Jia Ying
3	1.2	2020-11-10	Update Marking Information	Qi Shu Kun	Qi Shu Kun	Liu Jia Ying	Liu Jia Ying